

IN THE CLAIMS

1. (Original) A method of testing comprising:
disposing a first film of a first contact material on a substrate;
disposing a second film of a second contact material on a rounded end piece,
wherein a radius of curvature of the rounded piece along a contact surface between the
first film and the second film is higher than 10 μm and lower than 100 μm ; and
measuring a characteristic related to the first film and the second film contacting using at
least one measurement circuit to perform at least one measurement after the first film and the
second film contact each other at a controlled force.
2. (Original) The method according to claim 1 wherein the step of measuring the
characteristic related to the first film and the second film contacting occurs when the first film
and the second film contact with the controlled force not exceeding 10 μN .
3. (Original) The method according to claim 2 wherein the characteristic is a contact
resistance value.
4. (Original) The method according to 1 wherein the characteristic is a current-dependent
stiction force value and wherein the step of measuring the characteristic related to the first film
and the second film contacting occurs after the first film and the second film contact with the
controlled force and while the first film and the second film contact with a stiction measurement
force not exceeding 1 mN.
5. (Original) The method of claim 4 wherein the step of measuring the current-dependent
stiction force value is performed after passing a current higher than 5 μA and lower than 100 μA
through a contact interface between the first film and the second film when the first film and the
second film contact with the controlled force.